



In re Applicant: Alessia Pavan et al.

Art Unit:

2894

Serial No.:

10/749,130

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Filed:

December 30, 2003

Examiner:

Amar Movva

For:

Non-Volatile Memory Cell

Comprising Dielectric Layers

Having a Low Dielectric Constant and Corresponding

Docket:

NUM.0104US

02-AG-317

Manufacturing Process

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

REPLY TO OFFICE ACTION

Sir:

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In response to the office action mailed August 13, 2008, please amend the abovereferenced patent application as follows:

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with cient postage on the date indicated above and is addressed to the

Cynthia/L. Hayden